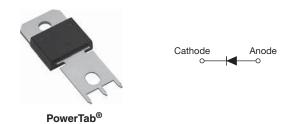


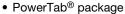
Ultrafast Soft Recovery Diode, 80 A FRED Pt®



PRODUCT SUMMARY				
Package	PowerTab [®]			
I _{F(AV)}	80 A			
V_{R}	400 V			
V _F at I _F	0.92 V			
t _{rr} (typ.)	See recovery table			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC®-JESD 47







RoHS

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V _R		400	V
Continuous forward current	I _{F(AV)}	T _C = 101 °C	80	
Single pulse forward current	I _{FSM}	T _C = 25 °C	800	А
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	160	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _r	Ι _R = 100 μΑ	400	-	-	
Forward voltage		I _F = 80 A	-	1.1	1.3	V
	V_{F}	I _F = 80 A, T _J = 175 °C	-	0.92	1.08	
		I _F = 80 A, T _J = 125 °C		0.98	1.15	
Reverse leakage current	I_	$V_R = V_R$ rated	-	-	50	μA
	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	92 1.08 98 1.15 - 50 - 2 r	mA
Junction capacitance	C _T	V _R = 200 V	-	50	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 3.5 -		nH		



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	50	60	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	87	-	ns
		T _J = 125 °C	$I_F = 80 \text{ A}$ $V_R = 200 \text{ V}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	151	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	9.3	-	Α
		T _J = 125 °C		-	17.2	1	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	405	-	nC
		T _J = 125 °C		_	1300	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.70	°C/W
Thermal resistance, junction to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	C/VV
Woight			-	-	5.02	g
Weight			-	0.18	-	OZ.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab®		80EE	3U04	

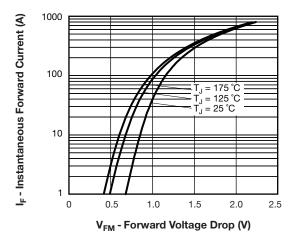


Fig. 1 - Maximum Forward Voltage Drop Characteristics

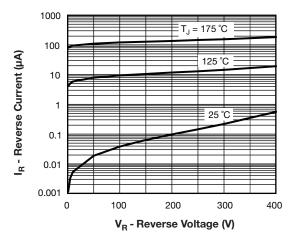


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



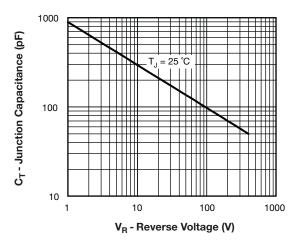


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

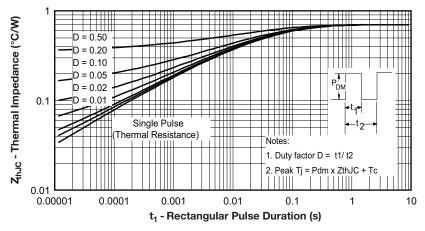


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

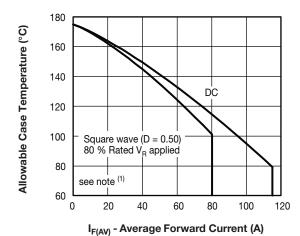


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

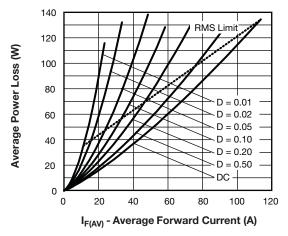


Fig. 6 - Forward Power Loss Characteristics



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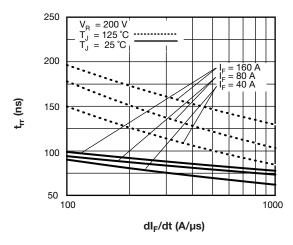


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

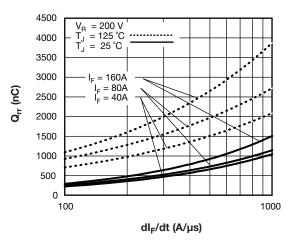


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = 80 \text{ \% rated } V_R \\ \end{array}$

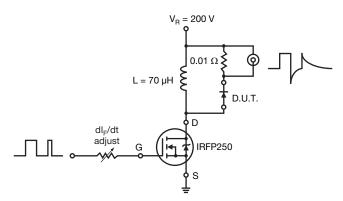
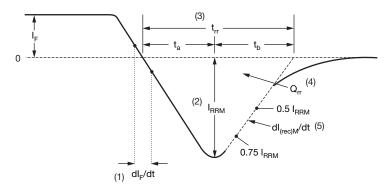


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

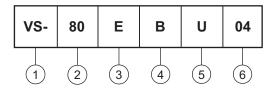
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



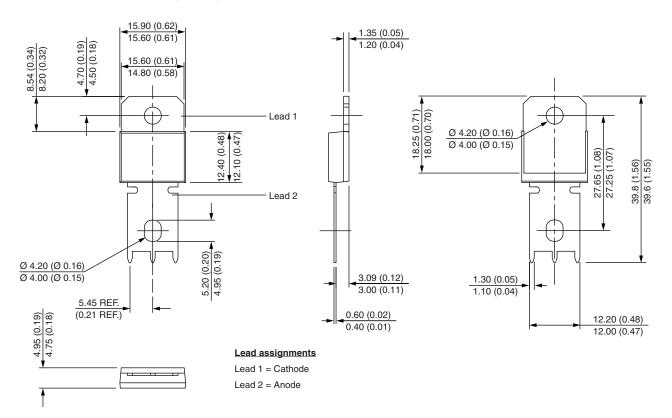
- 1 Vishay Semiconductors product
- Current rating (80 = 80 A)
- 3 E = Single diode
- B = PowerTab[®] (ultrafast/hyperfast only)
- 5 U = Ultrafast recovery
- 6 Voltage rating (04 = 400 V)

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95240</u>				
Part marking information	www.vishay.com/doc?95370			
Application note	www.vishay.com/doc?95179			



PowerTab[®]

DIMENSIONS in millimeters (inches)





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